

Title (en)

Self-supported ultra thin silicon wafer process

Title (de)

Verfahren zur Herstellung eines selbsttragenden ultradünnen Siliziumwafer

Title (fr)

Procédé de fabrication d'une rondelle de silicium ultra fine et auto-soutenue

Publication

EP 1061584 A3 20010613 (EN)

Application

EP 00110510 A 20000517

Priority

US 33483599 A 19990617

Abstract (en)

[origin: EP1061584A2] A silicon wafer 2 has an ultra thin central portion 2 that is supported by a circumferential rim 3 of thicker silicon. The central region is thinned by conventional means using conventional removal apparatus. As an alternative method, the central portion is removed using a photoresist mask or a combination of a photoresist mask and a hard mask. <IMAGE>

IPC 1-7

H01L 29/06; **H01L 21/308**

IPC 8 full level

H01L 21/302 (2006.01); **H01L 21/02** (2006.01); **H01L 21/306** (2006.01); **H01L 21/3065** (2006.01); **H01L 21/308** (2006.01); **H01L 21/336** (2006.01); **H01L 21/76** (2006.01); **H01L 29/78** (2006.01)

CPC (source: EP KR US)

H01L 21/02035 (2013.01 - EP US); **H01L 21/308** (2013.01 - EP US); **H01L 21/76** (2013.01 - KR)

Citation (search report)

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DOCDB simple family (application)

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